

WE CLAIM:

1. A leadframe for use in the assembly of integrated
5 circuit chips, comprising:
a base metal structure having an adherent layer of
nickel covering said base metal;
an adherent film of palladium on said nickel layer;
and
10 an adherent layer of palladium on said palladium
film, selectively covering areas of said
leadframe suitable for bonding wire attachment
and solder attachment.
- 15 2. The leadframe according to Claim 1 wherein said
base metal is selected from a group consisting of
copper, copper alloy, aluminum, iron-nickel alloy,
brass, or invar.
- 20 3. The leadframe according to Claim 1 wherein said nickel
layer has a thickness in the range from approximately 1
to 3 μm .
- 25 4. The leadframe according to Claim 1 wherein said nickel
layer is a stack consisting of a nickel layer in the
thickness range from about 30 to 50 nm, plated onto
said base metal, followed by a palladium/nickel layer
in the thickness range from about 30 to 50 nm, followed
by a nickel layer in the thickness range from about 1.0
to 3.0 μm .
5. The leadframe according to Claim 1 wherein said
palladium film has a thickness from about 1 to 5 nm.
- 30 6. The leadframe according to Claim 1 wherein said
palladium layer has a thickness from about 70 to 90 nm.
7. The leadframe according to Claim 1 wherein said

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palladium layer covers selective areas having
boundaries of loose tolerance.

8. The leadframe according to Claim 1 wherein said
palladium layer provides visual distinction to the
areas covered by said layer.
9. The leadframe according to Claim 1 wherein said base
metal has a thickness between about 100 and 250 μm .
10. The leadframe according to Claim 1 wherein said solder
attachment comprises materials selected from a group
consisting of tin/lead, tin/indium, tin/silver, tin/
bismuth, tin/copper, tin/silver/copper, and conductive
adhesive compounds.
11. The leadframe according to Claim 10 wherein said solder
layer has a reflow temperature compatible with wire
bonding temperatures and molding temperatures.
12. A semiconductor device comprising:
 - a leadframe comprising a chip mount pad for an
integrated circuit chip and a plurality of lead
segments, each segment having a first end near
said mount pad and a second end remote from said
mount pad;
 - said leadframe having an adherent layer of nickel;
 - said leadframe further having an adherent palladium
film on said nickel layer;
 - said leadframe further having an adherent layer of
palladium on said palladium film, selectively
covering said second ends of said lead segments
in a thickness suitable for solder attachment,
and further selectively covering the bonding wire
attachment areas on said first ends of said lead
segments in a thickness suitable for bonding wire
attachment;

an integrated circuit chip attached to said mount
pad;

bonding wires interconnecting said chip and said
first ends of said lead segments; and

5 encapsulation material surrounding said chip,
 bonding wires and said first ends of said lead
 segments, while leaving said second ends of said
 lead segments exposed.

10 13. The device according to Claim 12 wherein said bonding
 wires are selected from a group consisting of gold,
 copper, aluminum and alloys thereof.

15 14. The device according to Claim 12 wherein the bonding
 wire contacts to said first ends of said lead segments
 comprise welds made by stitch bonds, ball bonds, or
 wedge bonds.

15 15. The device according to Claim 12 wherein said
 encapsulation material is selected from a group
 consisting of epoxy-based molding compounds suitable
 for adhesion to said leadframe.

20 16. The device according to Claim 12 further comprising
 lead segments having said second ends bent, whereby
 said segments obtain a form suitable for solder
 attachment.

25 17. A method for fabricating a leadframe having first and
 second surfaces, a chip mount pad, and a plurality of
 lead segments, each segment having a first end near
 said mount pad and a second end remote from said mount
 pad, comprising the steps of:

30 plating a layer of nickel on said leadframe;
 masking said first surface to selectively expose
 said first and second segment ends;
 plating a thick layer of palladium on said nickel

layer to selectively cover said exposed first and
second segment ends to a thickness suitable for
bond wire attachment and solder attachment, and
plating a thin film of palladium on said nickel
layer fully covering said first surface;
masking said second surface to selectively expose
said second segment ends; and
plating a layer of palladium on said nickel layer on
said exposed second segment ends in a thickness
suitable for solder attachment, and plating a
thin film of palladium on said nickel layer fully
covering said second surface.

18. A method for fabricating a leadframe of copper or
copper alloy, having first and second surfaces, a mount
pad for an integrated circuit chip, and a plurality of
lead segments having their first end near said mount
pad and their second end remote from said mount pad,
comprising the steps of:

cleaning said leadframe in alkaline soak cleaning
and alkaline electrocleaning;
activating said leadframe by immersing said
leadframe into an acid solution, thereby
dissolving any copper oxide;
immersing said leadframe into a first electrolytic
nickel plating solution and depositing a first
layer of nickel onto said copper, thereby fully
encasing said copper;
immersing said leadframe into a palladium/nickel
plating solution and depositing a palladium/
nickel alloy layer onto said first nickel layer;
immersing said leadframe into a second electrolytic
nickel plating solution and depositing a second

layer of nickel onto said palladium/nickel layer,
thereby adapting said second ends of said lead
segments for mechanical bending;

masking said first surface to selectively expose

5 said first and second segment ends;

spraying said leadframe with an electrolytic

palladium plating solution to selectively cover

said exposed first and second segment ends to a

thickness suitable for bond wire attachment and

10 solder attachment, and to deposit a thin film of

palladium on said nickel layer fully covering

said first surface;

masking said second surface to selectively expose

said second segment ends; and

15 spraying said leadframe with an electrolytic

palladium plating solution to selectively cover

said exposed second segment ends to a thickness

suitable for solder attachment, and to deposit a

thin film of palladium on said nickel layer fully

20 covering said second surface.

19. The method according to Claim 18 wherein the process
steps are executed in sequence without time delays, yet
including intermediate rinsing steps.

20. The method according to Claim 18 wherein said acid
25 solution may be sulfuric acid, hydrochloric acid or any
other acid.

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